

Q2, 2023 Quarterly Reliability Report

1. S34ML-1 product family, 41nm SLC NAND

41 nm SLC NAND were introduced in Jun 2012 and utilize tunnel Oxide, Polysilicon floating gate and interconnections are three metal layers with contact plugs and barrier metals. The 1st Metal layer for 41 nm SLC NAND is using Copper.

Data Summary and Failure Rate Estimation using Exponential Model HTOL Stress Temperature - 125°C

| | | int / Test sult | | Modeling | Average Failure Rate | | | | |
|-----------------------------------|---------------------|------------------------|----------|----------|----------------------|-----|---------------|---------------------|-------------------------|
| Failure Mechanisms | Early Life (hrs) | Inherent Life (hrs) | Ea eV | TAF | VAF | OAF | MTTF (yrs) | Early Life (PPM) | Inherent Life (FITS) |
| | 96 | 1000 | | | | | (j.c) | () | (|
| Sample Size | 500 | 150 | | | | | | | |
| 125C, Zero fails, Process ave. Ea | 0 | 0 | 0.7 | 74 | 1 | 74 | | 0 | 12 |
| | | | | | | | 9259 | | |

Data Retention Bake - 150°C

| Reliability Stress | Sample Size | Reject | РРМ | FITS |
|--------------------|-------------|--------|-----|------|
| 1000 | 77 | 0 | 0 | <1 |

Endurance - 90°C

| Reliability Stress | Sample Size | Reject | РРМ | FITS |
|--------------------|-------------|--------|-----|------|
| 10000 | 60 | 0 | 0 | 0 |
| 100000(Decade) | 64 | 0 | 0 | 2 |



2. S34ML-2 product family, 32nm SLC NAND

32 nm SLC NAND were introduced in October 2012 and utilize tunnel Oxide, Polysilicon floating gate and interconnections are three metal layers with contact plugs and barrier metals. The 1st Metal layer for 32 nm SLC NAND is using Copper

Data Summary and Failure Rate Estimation using Exponential Model HTOL Stress Temperature - 125°C

| | Read Point / Test Result | | | Modelin | Average Failure Rate | | | | |
|-----------------------------------|-----------------------------|------------------------|----------|---------|----------------------|-----|---------------|---------------------|-------------------------|
| Failure Mechanisms | Early Life (hrs) | Inherent Life (hrs) | Ea eV | TAF | VAF | OAF | MTTF (yrs) | Early Life (PPM) | Inherent Life (FITS) |
| | 96 | 1000 | | | | | (913) | () | (110) |
| Sample Size | 500 | 150 | | | | | | | |
| 125C, Zero fails, Process ave. Ea | 0 | 0 | 0.7 | 74 | 1 | 74 | | 0 | 9 |
| | | | | | | | 12198 | | |

Data Retention Bake - 150°C

| Reliability Stress | Sample Size | Reject | РРМ | FITS |
|--------------------|-------------|--------|-----|------|
| 1000 | 77 | 0 | 0 | <1 |

Endurance - 90°C

| Reliability Stress | Sample Size | Reject | РРМ | FITS |
|--------------------|-------------|--------|-----|------|
| 10000 | 60 | 0 | 0 | 0 |
| 100000(Decade) | 64 | 0 | 0 | Z |



3. S34/S35ML-3 product family, 16nm SLC NAND

16 nm SLC NAND were introduced in November 2019 and utilize tunnel Oxide, Polysilicon floating gate and interconnections are three metal layers with contact plugs and barrier metals. The 1st Metal layer for 16 nm SLC NAND is using Copper

Data Summary and Failure Rate Estimation using Exponential Model HTOL Stress Temperature - 125°C

| · · · · · · · · · · · · · · · · · · · | Read Point / Test Result | | | Modelin | Average F | Average Failure Rate | | | |
|---------------------------------------|-----------------------------|------------------------|----------|---------|-----------|----------------------|---------------|---------------------|-------------------------|
| Failure Mechanisms | Early Life (hrs) | Inherent Life (hrs) | Ea eV | TAF | VAF | OAF | MTTF (yrs) | Early Life (PPM) | Inherent Life (FITS) |
| | 96 | 1000 | | | | | (313) | () | (110) |
| Sample Size | 500 | 150 | | | | | | | |
| 125C, Zero fails, Process ave. Ea | 0 | 0 | 0.66 | 61 | 1 | 62 | | 79 | 20 |
| | | | | | | | 5708 | | |

Data Retention Bake - 150°C

| Reliabil | lity Stress | Sample Si | ze | Reject | РРМ | FITS |
|----------|-------------|-----------|----|--------|-----|------|
| 1 | 000 | 77 | | 0 | 0 | <1 |

Endurance - 90°C

| Reliability Stress | Sample | Size | Reject | РРМ | FITS |
|--------------------|--------|------|--------|-----|------|
| 10000 | 60 | | 0 | 0 | 2 |
| 100000(Decade) | 64 | | 0 | 0 | 2 |



4. S40FC004 product family, 4GB eMMC

4GB eMMC were introduced in November 2020 and utilize tunnel Oxide, Polysilicon floating gate and interconnections are three metal layers with contact plugs and barrier metals. The 1st Metal layer for 16 nm MLC NAND is using Copper

Data Summary and Failure Rate Estimation using Exponential Model HTOL Stress Temperature - 125°C

| | Read Poir | nt / Test Res | ult | | Modeling Parameters @ 55°C | | | | | | |
|--------------------------------------|---------------------|---------------------|------|-------|----------------------------|-----|-----|---------------|---------------------|------------------|--|
| Failure Mechanisms | Early Life (hrs) | Inherent Life (hrs) | | Ea eV | TAF | VAF | OAF | MTTF (yrs) | Early Life (PPM) | Inherent Life | |
| | 168 | 504 | 1000 | | | | | (j.0) | () | (FITS) | |
| Sample Size | 231 | 231 | 231 | | | | | | | | |
| 125C, Zero fails, Process ave. Ea | | 0 | 0 | 0.7 | 61 | 1 | 62 | | 58.51 | 23.26 | |
| | | | | | | | | 3747 | | | |

Data Retention Bake - 150°C

| Reliability Stress | Sample Size | | Reject | РРМ | FITS |
|--------------------|-------------|--|--------|-----|------|
| 1000 | 77 | | 0 | 0 | <1 |

Endurance - 90°C

| Reliability Stress | Sample | Size | | Reject | РРМ | FITS |
|--------------------|--------|------|--|--------|-----|------|
| 10000 | 60 | | | 0 | 0 | 2 |
| 100000(Decade) | 64 | | | 0 | 0 | 2 |



5. Data Summaries by PackageFamily BGA 63 (Ball Grid Array)

| Reliability Stress | | Sample Size | Reject | Failure Rate PPM |
|--------------------|-----------|----------------|--------|---------------------|
| HAST | 96hrs | 433 | 0 | 0 |
| | 264hrs | 557 | 0 | 0 |
| HIGH TEMP STORAGE | 1000hrs | 770 | 0 | 0 |
| TEMP CYCLE | 500cycle | 563 | 0 | 0 |
| | 1000cycle | 75 | 0 | 0 |
| UNBIASED HAST TEST | 96hrs | 611 | 0 | 0 |
| | 264hrs | 173 | 0 | 0 |

TSOP 48 (Thin Small Outline Package)

| Reliability Stress | | Sample Size | Reject | Failure Rate PPM |
|----------------------|----------|----------------|--------|---------------------|
| HAST | 96hrs | 490 | 0 | 0 |
| | 264hrs | 120 | 0 | 0 |
| HIGH TEMP STORAGE | 1000hrs | 847 | 0 | 0 |
| PRESSURE COOKER TEST | 96hrs | 500 | 0 | 0 |
| | 168hrs | 30 | 0 | 0 |
| TEMP CYCLE | 500cycle | 490 | 0 | 0 |
| UNBIASED HAST TEST | 96hrs | 435 | 0 | 0 |

BGA 153 (Ball Grid Array)

| Reliability Stress | | Sample Size | Reject | Failure Rate PPM |
|--------------------|----------|----------------|--------|---------------------|
| PC | 192hrs | 693 | 0 | 0 |
| HAST | 164hrs | 231 | 0 | 0 |
| HIGH TEMP STORAGE | 1000hrs | 231 | 0 | 0 |
| TEMP CYCLE | 500cycle | 231 | 0 | 0 |
| UNBIASED HAST TEST | 96hrs | 231 | 0 | 0 |